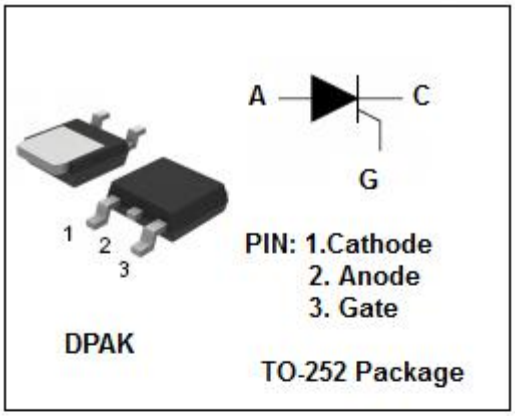
isc Thyristors 2P4M-D

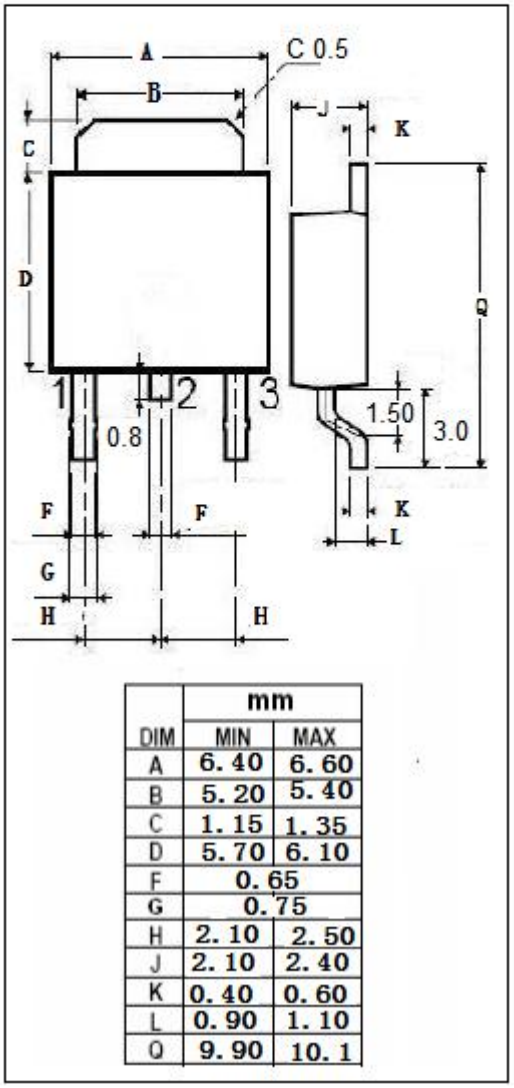


DESCRIPTION

- The 2P4M is P-gate all diffused plastic molded type SCR granted average on-state current 2A(T_C=77℃)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Highly sensitive triggering levels
- Solid state switches etc
- Automatic gas lighter,battery charger
- For capacitive discharge ignitions, motor control in kitchen aids, over voltage crowbar protection in low power supplies applications.



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	400	V
V_{RRM}	Repetitive peak reverse voltage	400	V
$I_{T(AV)}$	On-state current 180 ° conduction angle	2	A
I_{TSM}	Non-repetitive surge peak on-state current t= 20ms	20	A
$P_{G(AV)}$	Average gate power dissipation T_j = 125℃	0.1	W
T_j	Junction temperature	125	℃
T_{stg}	Storage temperature	-40 to + 150	℃

isc Thyristors 2P4M-D

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	$V_{RM}=V_{RRM}$, R_{GK}=1kΩ ,Tj=125℃		100	μA
I_{DRM}	Repetitive peak off-state current	$V_{DM}=V_{DRM}$,R_{GK}=1kΩ ,Tj=125℃		100	μA
V_{TM}	On-state voltage	I_{TM}= 4A		2.2	V
I_{GT}	Gate-trigger current	V_{DM}=6V;R_L=100Ω		200	μA
V_{GT}	Gate-trigger voltage	V_{DM}=6V;R_L=100Ω		0.8	V